

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14261	etch\$3 near3 (sacrificial dielectric) and (gate with (sacrificial dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09 13:46
L2	36796	((substrate or wafer) with (dielectric or oxide or insulat \$3 or ILD IMD ) with (gate polysilicon electrode) with (sacrificial dielectric or oxide or insulat \$3 or ILD IMD )) and (remov\$3 etch \$3) near1 (sacrificial dielectric or oxide or insulat \$3 or ILD IMD )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09 13:46
L3	7039	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09 13:47

10/ 9/ 2008 1:47:16 PM

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